## NSN 5961-00-405-1169

Diode Semiconductor Device - Page 1 of 1



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| Inclosure Material:  |
|--|
| Glass  |
| Function For Which Designed:   |
| Microwave  |
| End Application:   |
| Aircraft, f-11; strategic weapon systems (poseidon and trident); los angeles class ssn (688); spruance class dd (963); wasp class lhd; |
| tarawa class lha; yellowstone class ad-41; general purpose electronic test equipment gpete; forrestal class cv; emory s. Land class as |
| Features Provided:   |
| Hermetically sealed case   |
| Criticality Code Justification:  |
| Feat   |
| Semiconductor Material:  |
| Silicon  |
| Voltage Rating In Volts Per Characteristic:  |
| 20.0 breakover voltage, dc   |
| Capacitance Rating In Picofarads:  |
| 2.2  |
| Special Features:  |
| Weapon system essential  |
| Shelf Life:  |
| N/a  |
| Unit Of Measure:   |
|  |
| Demilitarization:  |
| No   |
| Fiig:  |
| A110a0   |
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